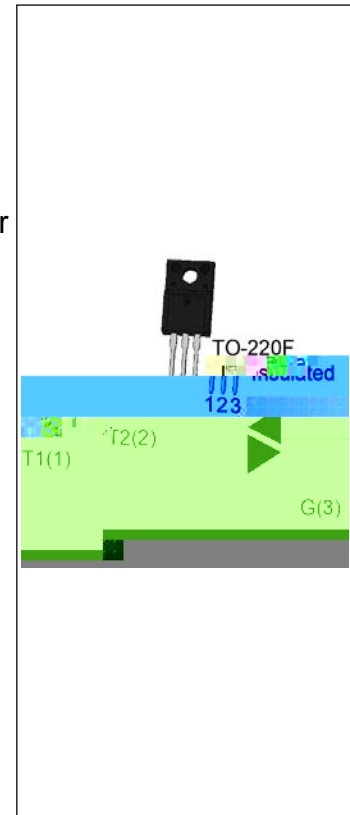


The JST12F-1200BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST12F-1200BW snubberless triac is especially recommended for use on inductive loads. By using an external plastic package, JST12F-1200BW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	1200	V
$I_{GT} / /$	50/50/50	mA

Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1200	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1200	V
RMS on-state current ($T_c=85^\circ\text{C}$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	120	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		132	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2\text{hI}_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)	$P_{G(AV)}$	0.5	W



Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4.5	kV

($T_j=25$ unless otherwise specified)

I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	70	mA
				90	
I_H	$I_T=500mA$		MAX.	50	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$		MIN.	500	V/ μs
(dI/dt)c	(dV/dt)c=20V/ μs $T_j=125$		MIN.	20	A/ms
t_{on}	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25$		TYP.	5	μs
t_{off}				50	

V_{TM}	$I_{TM}=17A t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.78	V
R_D	Dynamic resistance	$T_j=125$	37	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	10	μA
I_{RRM}		$T_j=125$	2	mA

$R_{th(j-c)}$	junction to case (AC)	2.4	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W



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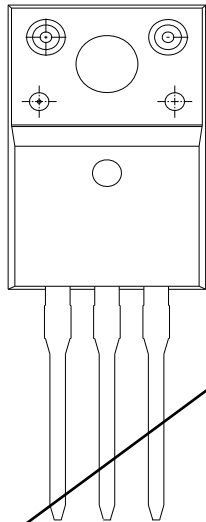
J **ST** **12** **F** **-1200** **BW**

Triacs
I_{T(RMS)}:12A

F:TO-220F(Ins)

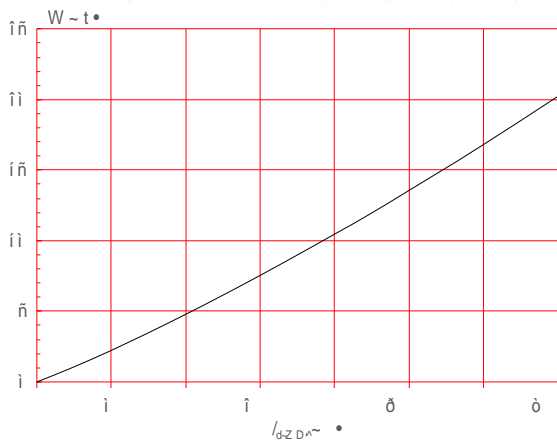
BW:IGT1-3 0.50mA

1200:V_{DRM} /V_{RRM} 1 1200V

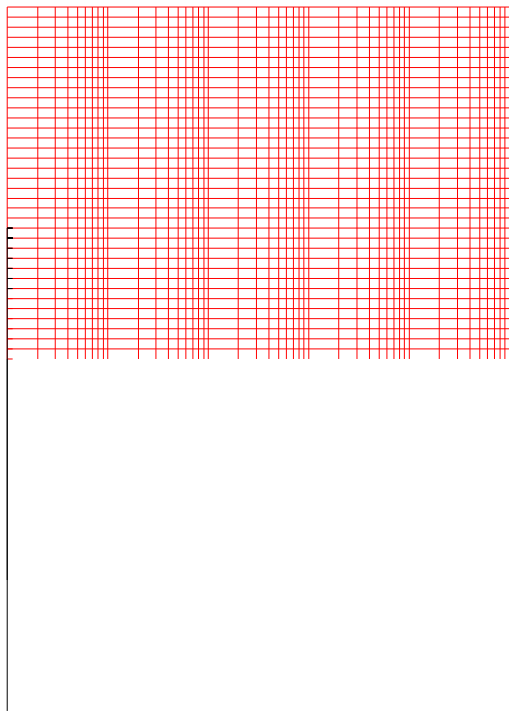




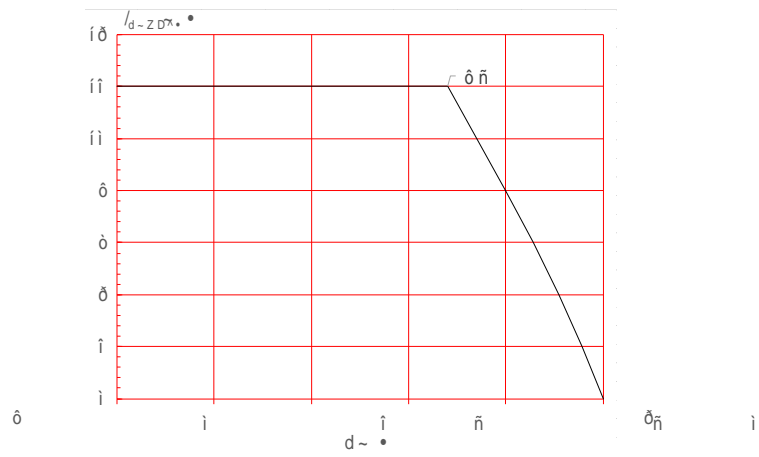
Maximum power dissipation versus RMS on-state current



Surge peak on-state current versus number of cycles

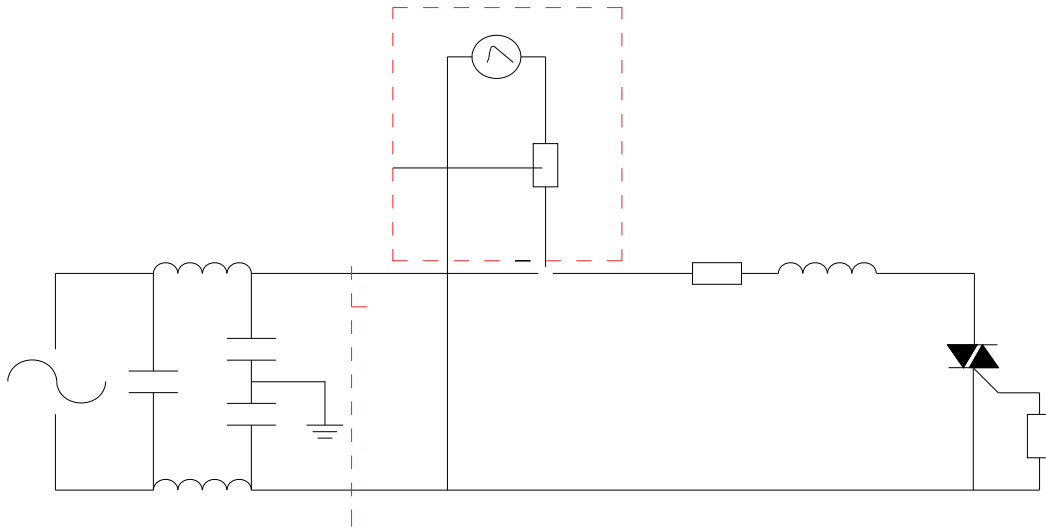


RMS on-state current versus case temperature



On-state characteristics

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards





Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated
Oct.13, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA





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